Features

- Split Gate Trench MOSFET Technology
- Excellent Package For Heat Dissipation
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device(Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-Channel MOSFET

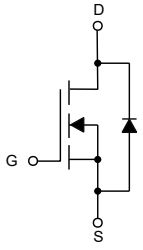
Maximum Ratings

- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 40°C/W Junction to Ambient(Note 2)
- Thermal Resistance:1.38°C/W Junction to Case

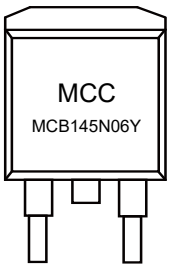
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	145	A
	T_C=100°C		92	
Pulsed Drain Current(Note 3)		I_{DM}	580	A
Total Power Dissipation(Note 4)		P_D	91	W
Single Pulsed Avalanche Energy(Note 5)		E_{AS}	144	mJ

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. T_J=25°C, V_{DD}=40V, V_{GS}=10V, L=0.5mH.

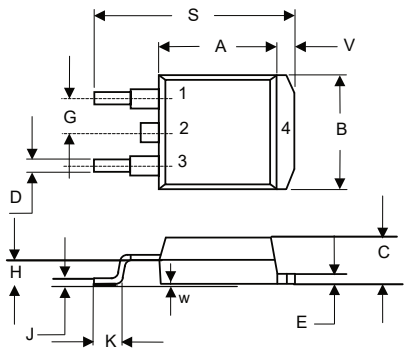
Internal Structure and Marking Code



1. Gate
2,4. Drain
3. Source

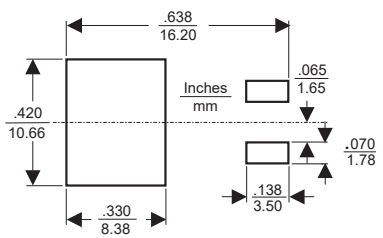


D2-PAK



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.331	0.370	8.40	9.40	
B	0.378	0.417	9.60	10.60	
C	0.165	0.189	4.20	4.80	
D	0.027	0.037	0.68	0.94	
E	0.045	0.055	1.14	1.40	
G	0.1		2.54		TYP.
H	0.096	0.134	2.43	3.40	
J	0.011	0.025	0.28	0.64	
K	0.071	0.131	1.80	3.32	
S	0.575	0.625	14.60	15.87	
V	0.042	0.058	1.07	1.47	
W	0.000	0.010	0.00	0.25	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	60			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1.2	1.7	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A		5.3	7.5	mΩ
		V_{GS}=4.5V, I_D=10A		6.9	9.5	
Gate Resistance	R_g	f=1 MHz, Open drain		1.5		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				145	A
Body Diode Voltage	V_{SD}	I_S=20A, V_{GS}=0V			1.2	V
Reverse Recovery Time	t_{rr}	I_F=20A di/dt=200A/μs		32		ns
Reverse Recovery Charge	Q_{rr}			52		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=35V,V_{GS}=0V,f=100KHz		1913		pF
Output Capacitance	C_{oss}			380		
Reverse Transfer Capacitance	C_{rss}			15		
Total Gate Charge	Q_g	V_{DS}=30V,I_D=20A V_{GS}=10V		32		nC
Gate-Source Charge	Q_{gs}			4.8		
Gate-Drain Charge	Q_{gd}			5.9		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=30V,V_{GS}=10V,I_D=12A R_G=3Ω		8.5		ns
Turn-On Rise Time	t_r			12		
Turn-Off Delay Time	$t_{d(off)}$			29		
Turn-Off Fall Time	t_f			9.2		

Curve Characteristics

Fig.1 - Typical Output Characteristics

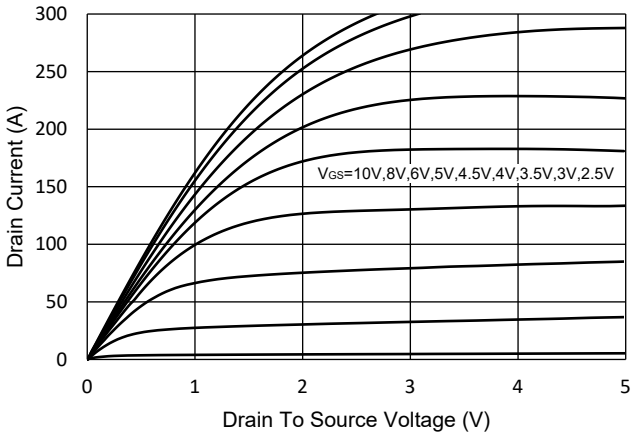


Fig.2 - Transfer Characteristic

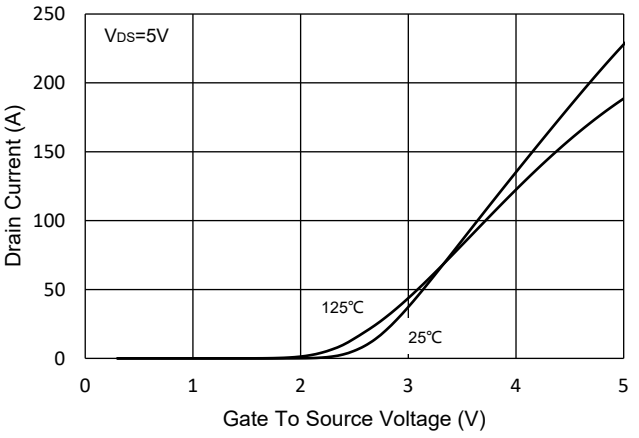


Fig.3 - $R_{DS(ON)}$ - V_{GS}

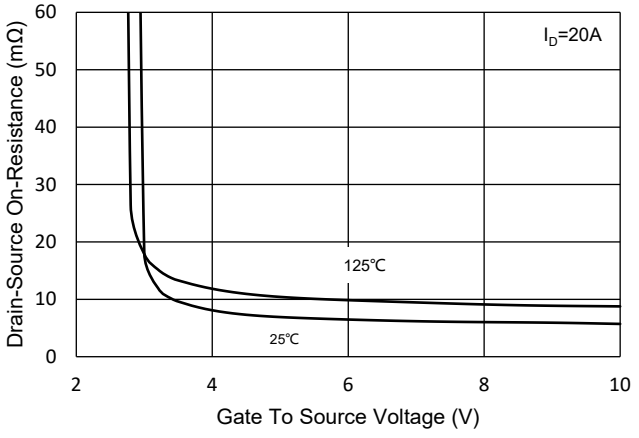


Fig.4 - $R_{DS(ON)}$ - I_D

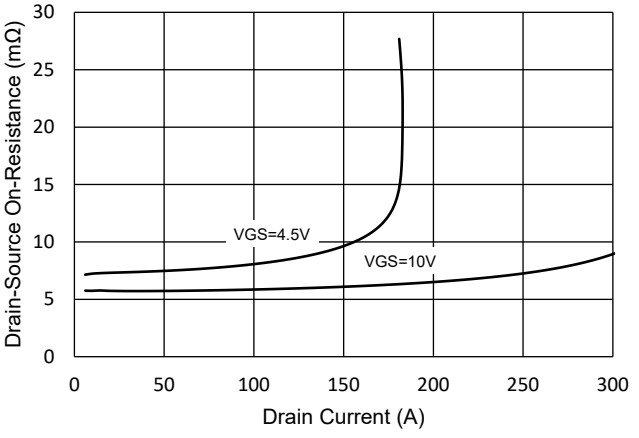


Fig.5 - Capacitance Characteristics

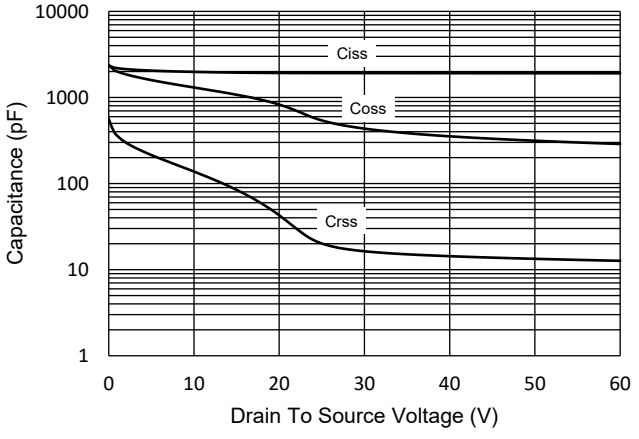
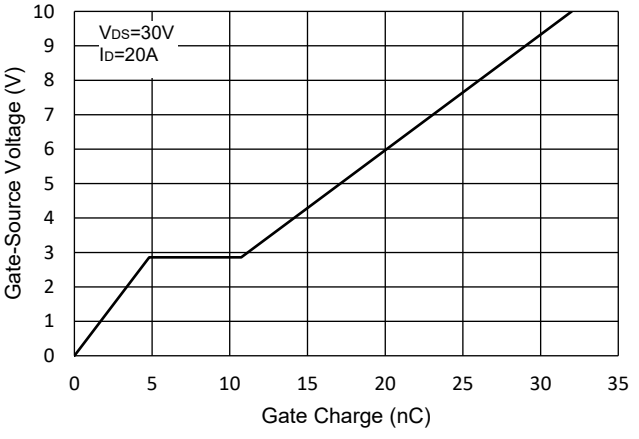


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

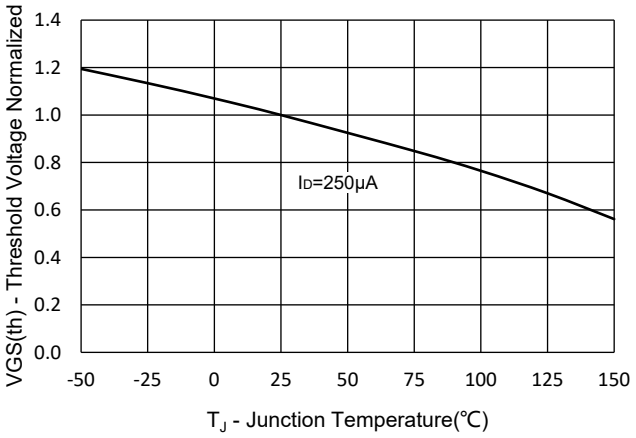


Fig.8 - Normalized On Resistance Characteristics

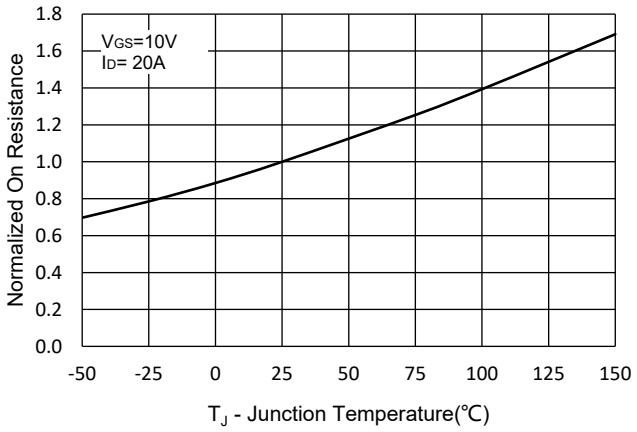


Fig.9 - I_S - V_{SD}

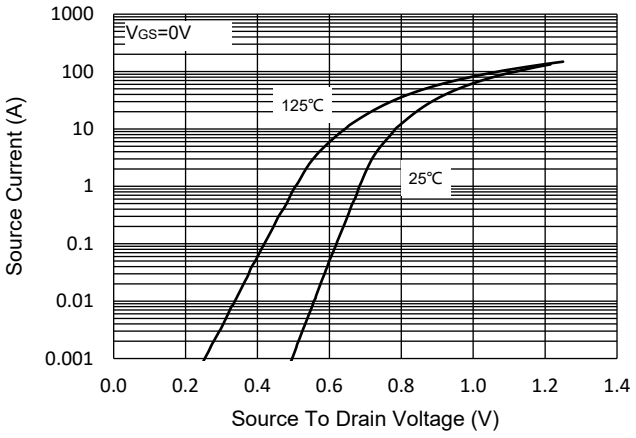


Fig.10 - Drain Current

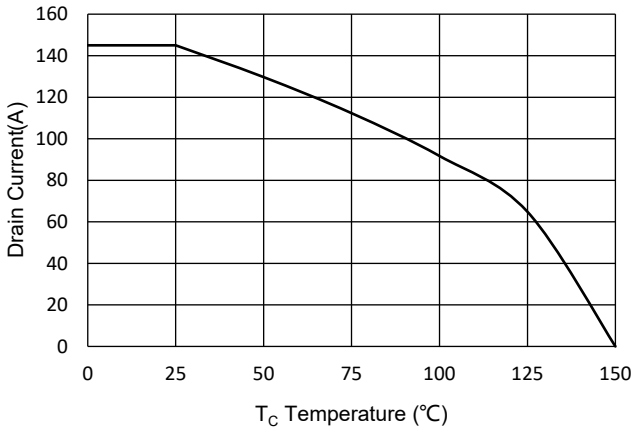
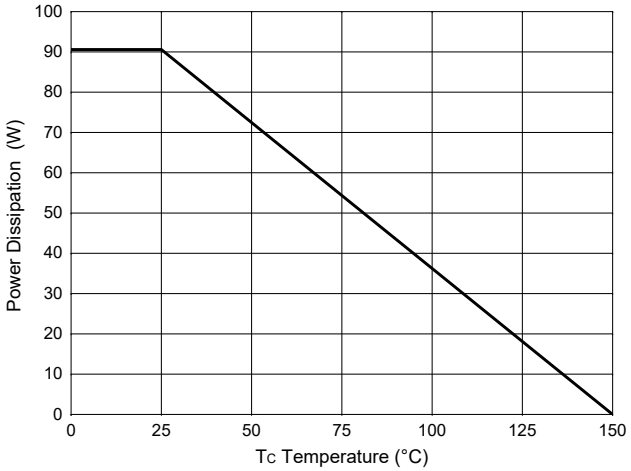


Fig.11-PD Dissipation



Curve Characteristics

Fig.12 - Safe Operation Area

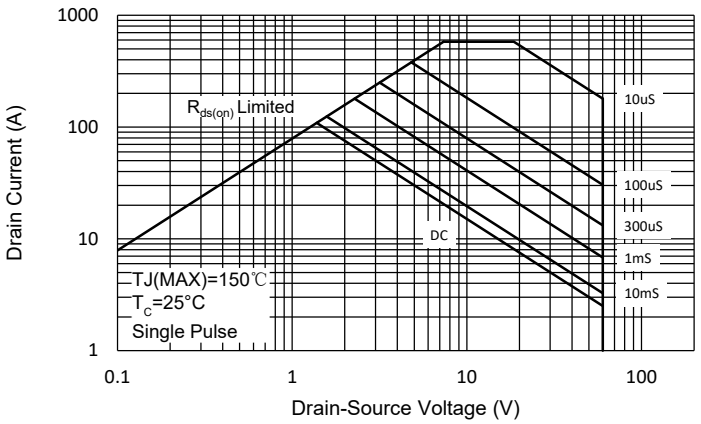
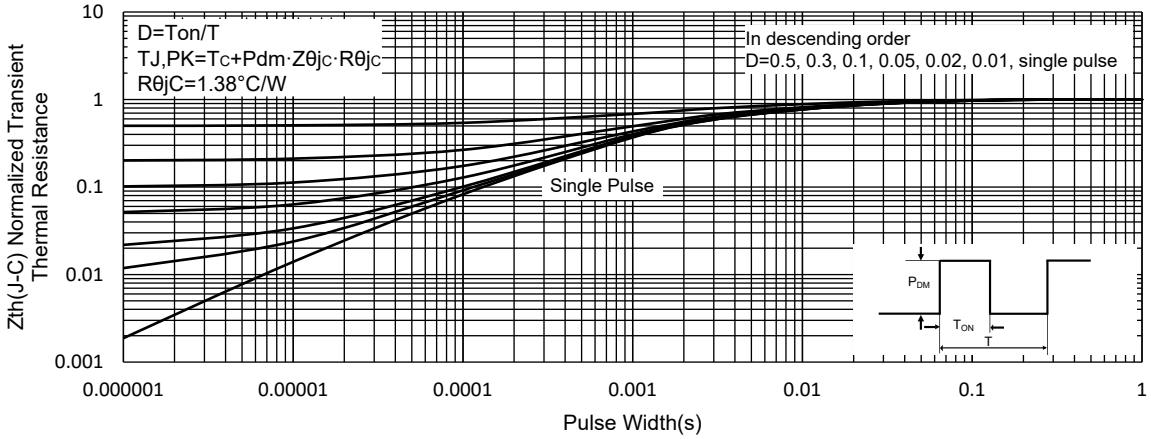


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 800pcs/Reel